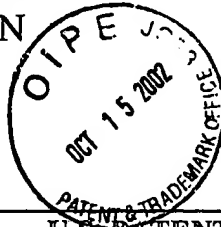


INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)



ATTY. DOCKET NO.
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09/610,640

APPLICANT
Koji ERIGUCHI, et al.

FILING DATE
July 05, 2000

GROUP
2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>CME</i>	4,547,074	10/15/85	Hinoda et al.	356	405	5/7/82
<i>CME</i>	5,020,910	6/4/91	Dunn et al.	356	328	3/5/90
<i>CME</i>	5,877,860	3/2/99	Borden	356	376	5/13/96
<i>CME</i>	6,128,084	10/3/00	Nanbu et al.	356	369	6/10/98
<i>CME</i>	6,141,103	10/31/00	Pinaton et al.	356	369	3/17/99
<i>CME</i>	6,175,416 B1	1/16/01	Maris et al.	356	381	8/24/99
<i>CME</i>	5,260,772	11/9/93	Pollak et al.	356	417	7/20/89
<i>CME</i>	5,748,318	5/5/98	Maris et al.	356	381	8/6/96

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>CME</i>	63222473	9/16/88	JPO	438	80	X	
<i>CME</i>	62119422	5/30/87	JPO	356	43	X	
<i>CME</i>	0768512 A2	4/16/97	EPO	—	—	X	
<i>CME</i>	6035578	2/23/85	JPO	356	52	X	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

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C. Suerbaert

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

**INFORMATION DISCLOSURE
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(PTO-1449)

ATTY. DOCKET NO.
43889-951

SERIAL NO.
**(Divisional of Serial No.
08/965,892)
09/610,440**

APPLICANT
Koji ERIGUCHI, et al.

FILING DATE
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U.S. PTO
09/610,440
07/05/00

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>CME</i>	4,652,757	3/87	Carver	-	-	-
<i>CME</i>	4,750,822	6/88	Rosencwaig et al.	-	-	-
<i>CME</i>	5,260,772	11/93	Pollak et al.	-	-	-
<i>CME</i>	5,536,936	7/96	Drevillon et al.	-	-	-
<i>CME</i>	4,211,488	7/80	Kleinknecht	-	-	-
<i>CME</i>	5,365,334	11/15/94	Bottka	-	-	-
<i>CME</i>	5,379,109	1/3/95	Gaskill et al.	-	-	-
<i>CME</i>	5,313,044	5/17/94	Massoud et al.	-	-	-
<i>CME</i>	5,314,831	5/24/94	Hirae et al.	-	-	-
<i>CME</i>	5,663,657	9/2/97	Lagowski et al.	-	-	-

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>CME</i>	0655620	11/29/94	Europe	-	-		

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>CME</i>	"Supervisory Run-To-Run Control of Polysilicon Gate Etch Using In Situ Ellipsometry", by Butlers et al., IEEE Transaction on Semiconductor Manufacturing, Vol. 7, No. 2, May 1, 1995, pp. 193-201.
<i>CME</i>	"Measurement of Damage Profile in Semiconductors: A Sensitive Optical Technique", by Shwe et al., Applied Physics Letters, Vol. 62, No. 5, February 1, 1993, pp. 516-518.

EXAMINER *C. Lushart*

DATE CONSIDERED **7-31-02**